Amendments to the Specification

Please substitute the following paragraph for paragraph [0017].

Figure 4 illustrates one embodiment of the present invention resulting in high impedance and high conductivity areas on a metallized area 400 within a mobile phone. In this embodiment electro-magnetic scattering 410 is attenuated at metallization edges by varying the metallization pattern 420. As the electro-magnetic waves scatter 410 towards the edge of the metallized area 400, they encounter progressively higher impedances 420 in the form of resistive materials. As a result, a higher impedance path is presented toward the edge of the metallized area 400, therefore resulting in attenuated electro-magnetic scattering 450 being emitted from the edge of the metallized area 400.

Please substitute the following paragraph for paragraph [0018].

Figure 5 illustrates another embodiment resulting in high impedance and high conductivity areas on a metallized area 400 within a mobile phone. In this embodiment electro-magnetic scattering 410 is attenuated at metallization edges by controlling the current path near the edge. Discrete components 520 such as resistors, inductors, or capacitors are used to control impedance. Strips of metallization 530 are used to control the current path that is followed by the scattering electro-magnetic surface waves 410. The discrete components 520 essentially obstruct the current path thereby attenuating the electro-magnetic waves by requiring them to use up much of their energy to get through the obstruction, therefore resulting in attenuated electro-magnetic scattering 550 being emitted from the edge of the metallized area 400.

Please substitute the following paragraph for paragraph [0019].

Figure 6 illustrates yet another embodiment resulting in high impedance and high conductivity areas on a metallized area 400 within a mobile phone. In this embodiment electro-magnetic scattering 410 is similarly attenuated at metallization edges by controlling the current path near the edge. This time, capacitive gaps 620 and inductive lines 630 are used to control the impedance near the edge. This results in the electro-

magnetic waves 410 having to expend significant energy to overcome the obstructions (capacitive gaps 620 and inductive lines 630) resulting in attenuated electro-magnetic scattering 650 being emitted from the edge of the metallized area 400.

Please substitute the following paragraph for paragraph [0020].

Figure 7 illustrates still another embodiment resulting in high impedance and high conductivity areas on a metallized area 400 within a mobile phone. In this embodiment electro-magnetic scattering 410 is again attenuated at metallization edges. Various degrees of conductivity layers 720 are used to control and vary impedance near the edge. Progressively higher impedances are encountered as the current from the scattering electro-magnetic waves flows toward the edge of the metallized area 400, therefore resulting in attenuated electro-magnetic scattering 750 being emitted from the edge of the metallized area 400.

Amendments to the Drawings

Figures 4-7 have been amended to further clarify the invention. Specifically, these figures have been amended to show that attenuated electro-magnetic scattering is emitted from the edge of the metallized areas. Replacement sheets for all figures are attached.